

2SA561 is PNP silicon, planar transistor designed for low power general purpose amplifiers.

TO-92B



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	150mA
Total Power Dissipation	Ptot	300mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ECB

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO	50		V	IC=10mA IB=0
Collector Cutoff Current	ICBO		100	nA	VCB=18V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=5V IC=0
D.C. Current Gain	HFE	70	400		IC=20mA VCE=1V
		70	140		
		120	240		
		200	400		
		23			IC=150mA VCE=5V*
		23			
		40			
		67			
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=100mA IB=10mA*
Current Gain Bandwidth Product	fT	70	TYP	MHz	IC=1mA VCE=6V
Output Capacitance	Cob	13	TYP	pF	VCB=6V f=1MHz

* Pulse Test : Pulse Width <300us, duty cycle <2%.



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